Escape of trapped electrons from a helium surface: a dynamical theory

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We present a dynamical theory which incorporates the electron-electron correlations and the electron escaping and the electron escaping from a helium surface. A nalytical expressions for the escape rate can be obtained in various limits. In particular, the tunneling rate with a parallel magnetic eld is presented explicitly.

The system of electrons in a metastable well near a helium surface is an ideal system to test our understanding of the escape process from a metastable well with many body correlations due to Coulomb interaction. A number of experiments have been performed on the escaping of electrons from a helium surface. Recent theoretical studies have mainly concentrated on how the static correlations a ect the escape rate. In the present paper we describe a dynamical theory for the escape of an electron from a helium surface, which accounts for the ects of both static and dynamical correlations as well as ofm agnetic elds.

W e consider the experim entally relevant situation in which the lifetime of the metastable state of an electron is much longer than its relaxation time in the metastable well and the density of 2-d electrons is low such that the Ferm item perature is the smallest energy scale in the problem. The escaping electrons are then statistically independent of each other and the exchange e ect of an escaping electron with 2-d electrons can be ignored. A separation between the escaping electron and the remaining 2-d electrons for each escape event can be made. Firstly we nd the effective Hamiltonian which describes the escape process in the high temperature limit. Starting from it we use an imaginary time path integral method to calculate the tunneling rate at low tem peratures. We shall ignore the weaker interactions between the escaping electron and the surface waves of liquid helium and the helium vapor atom s, which have been discussed elsewhere³.

The key element in the present theory is to

treat properly the dynam ics of the 2-d electrons in response to the motion of the escaping electron, which presents an induced electric force in the equation of motion for the escaping electron. The 2-d electron uid is described by a set of hydrodynam ical equations: the continuity equation and the Euler's equation. In the small density deviation and nonrelativistic lim it, we linearize the hydrodynam ical equations. We solve for the density deviation, which is determined by the motion of plasm a modes. Then using the Poisson equation we can calculate the induced electric eld3. At this point we nd that we are facing a problem similar to the one in the discussion of the macroscopic quantum e ect4, where the total Ham iltonian has three parts, a dissipative bath consisting of harm onic oscillators, a system of interest, and the coupling between the system and the bath. Using this analogy, we obtain the effective H am iltonian to describe the m otion of the escaping electron:5;3

$$H = \frac{1}{2m} P = \frac{e}{c} A_{ex} + V_{A}(z) + \sum_{k < k_{c}} X^{2} dk$$

$$\frac{p_{j}^{2}(k)}{2m} + \frac{m!_{p}^{2}(k)}{2} q_{j}(k) = \frac{(z)_{j}}{m!_{p}^{2}(k)}; (1)$$

with the adiabatic potential

$$V_A(z) = V_0(z) - \frac{1}{2} \int_0^{Z_{k_c}} dk \frac{2(z)}{n_0 e^2(1-4)};$$
 (2)

the plasma dispersion relation $!_{p}^{2}(k) = !_{B}^{2} + n_{0}e^{2}2 k(1) = p\frac{4}{n_{0}e^{4}} + k_{B}Tk^{2} + m_{0}Tk_{c} = 2^{p}\frac{1}{n_{0}} + k_{C} = 2^{p}\frac{1}{n_{0}}$, and (z) = $p\frac{4}{n_{0}e^{4}}(1 + 4) \exp f kzg$.

Here $!_B = eB_{?\,ex}$ =m c with $B_{?\,ex}$ the component of the external magnetic eld perpendicular to the helium surface. In the calculation the pressure $p = nk_B$ T for the 2-d classical electron uid phase has been used. The e ect due to p is small in the present problem. In eq.(1) m and e are the mass and the charge of an electron respectively, c is the speed of light, $_1 = \cos(k - r)$, $_2 = \sin(k - r)$, and $B_{ex} = r - A_{ex}$. In eq.(2) $V_0(z) = V_w(z) + V_1(z) + V_n(z)$, and V_w is the hardwall potential, $V_w = 1$ for z < 0, $V_w = 0$ for z > 0, which prevents electrons from entering the liquid helium. The image potential is $V_1 = e^2 = z$ with = (1)=4(+1) and the dielectric constant of liquid helium. The

the dielectric constant of liquid helium . The potential V_n is the total electric potential produced by the external applied electric eld (perpendicular only) and the electric eld produced by the mean density n_0 of the 2-d electrons, V_n (z) = e[E $_{\rm ex}$ + 2 e(1 4)n $_0$]z. The condition for 2-d electrons to escape from the surface to z = 1 is E $_{\rm ex}$ + 2 e(1 4)n $_0$ < 0.

If 2-d electrons completely follow the motion of the escaping electron, the so called adiabatic lim it, their responses are described by the adiabatic potential eq.(2). The deviation from the adiabatic response is described by the dynam ics of plasm a modes, the last term in eq.(1). The second term of eq.(2) corresponds to the correlation potential discussed in Ref.[1]. Hence an alternative justi cation of its usage in Ref.[1] is obtained here. Based on the e ective Hamiltonian, eq.(1), the number of degree of freedom in the the calculation of escape rate is e ectively reduced from original 3N to 3 after integration over plasm a modes, and analytical expressions can be obtained in various lim its. The Ham iltonian may have a wider application regime than that of the present hydrodynam ical approach. For instance, one m ay argue that eq.(1) can be applied to the Wigner lattice case. This would lead to the conclusion that there is no change of escape rate cross the melting temperature because there is no change of density uctuation. 5;3

For an illustration, we present the results for the situation $B_{kex} \notin 0$ and $B_{?ex} = 0.5$ In this case, there is no in uence on the thermal activation rate because the magnetic eld does not af-

fect the barrier height, if we ignore its sm alle ect on the ground state energy E_0 . For the quantum tunneling process, by a sem iclassical calculation we not that in the high eld lim it (The cyclotron frequency is larger than the binding energy) the tunneling rate is zero at zero tem perature. In the sm all eld and low tem perature lim it, the sem iclassical action can be evaluated perturbatively:

$$S_{c} = S_{c0} + \frac{1}{2m} \frac{eB_{kex}}{c}^{2} Z^{2} d z_{c}^{2} ()$$

$$\frac{1}{2m} \frac{eB_{kex}}{c}^{2} \frac{k_{B}T}{c}^{2} d z_{c}^{2} () ; (3)$$

with S_{c0} the sem iclassical action in the absence of the magnetic eld and the sem iclassical trajectory z_c () determined by the usual equation m $z_e^2 = 2 = V_A$ (z_c) E_0 . The tunneling rate is then expf $S_c = hg$. It should be emphasized that in the calculation leading to eq.(3) we have taken a full consideration of the 3-d dynamics of the escaping electron.

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